

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|--|---|------------------|---------|------------------|
| S1 | 585 | chalcogenide and memory and @ad<"20040203" and dielectric and electrode | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/01 16:44 |
| S2 | 167 | chalcogenide and memory and @ad<"20040203" and dielectric and electrode and pore | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/30 11:07 |
| S3 | 230 | (257/2).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/30 16:03 |
| S4 | 173 | (257/2).ccls. and @ad<"20040203" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/30 16:04 |
| S5 | 77 | chalcogenide and memory and @ad<"20040203" and dielectric and electrode and current and break | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/31 12:50 |
| S6 | 11 | chalcogenide and memory and @ad<"20040203" and dielectric and electrode and current and break and test | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/31 12:43 |
| S11 | 0 | chalcogenide and memory and @ad<"20040203" and dielectric and electrode and "two chalco" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/01 16:35 |
| S12 | 0 | chalcogenide and memory and @ad<"20040203" and dielectric and electrode and "both chalco" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/01 16:33 |

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| S13 | 20 | chalcogenide and memory and @ad<"20040203" and dielectric and electrode and "first chalcogenide" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/31 14:37 |
| S14 | 1 | "upper phase change resistor" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/31 14:43 |
| S15 | 15 | "phase change resistor" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/31 14:44 |
| S16 | 2 | chalcogenide and memory and @ad<"20040203" and dielectric and electrode and "upper chalcogenide" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/06 15:05 |
| S17 | 17 | chalcogenide and memory and @ad<"20040203" and dielectric and electrode and "top chalcogenide" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/01 09:19 |
| S18 | 19 | chalcogenide and memory and @ad<"20040203" and dielectric and electrode and "second chalcogenide" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/06 15:07 |
| S20 | 13275 | horii | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/01 16:36 |
| S21 | 6906 | horii.in. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/01 16:37 |

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| S22 | 11 | horii.in. and chalcogenide | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/01 16:40 |
| S23 | 5 | ha.in. and chalcogenide | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/02 12:12 |
| S24 | 528 | chalcogenide and memory and @ad<"20030720" and dielectric and electrode | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/01 16:46 |
| S25 | 528 | chalcogenide and memory and @ad<"20030720" and dielectric and electrode and pd<"20030720" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/01 16:47 |
| S27 | 292 | chalcogenide and memory and dielectric and electrode and @pd<"20030720" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/02 10:37 |
| S28 | 140 | "phase change material" and memory and dielectric and electrode and @pd<"20030720" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/02 13:43 |
| S29 | 86 | chen.in. and chalcogenide | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/02 12:22 |
| S30 | 9 | horii.in. and "phase change material" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/02 12:24 |

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| S31 | 5 | horak.in. and ("phase change material" or "chalcogenide") | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/02 12:25 |
| S32 | 1 | furkay.in. and ("phase change material" or "chalcogenide") | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/02 12:26 |
| S33 | 155 | johnson.in. and ("phase change material" or "chalcogenide") | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/02 12:36 |
| S34 | 13 | ha.in. and ("phase change material" or "chalcogenide") | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/02 12:38 |
| S35 | 281 | lee.in. and ("phase change material" or "chalcogenide") | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/02 12:38 |
| S36 | 287 | "memory material" and memory and dielectric and electrode and @pd<"20030720" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/02 13:43 |
| S37 | 20 | chalcogenide and memory and @ad<"20040203" and dielectric and electrode and "first chalcogenide" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/06 08:48 |
| S38 | 75 | chalcogenide and memory and @ad<"20030720" and (257/2).ccis. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/06 08:49 |

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| S39 | 82 | chalcogenide and @ad<"20030720" and (257/2).ccls. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/06 09:18 |
| S40 | 87 | chalcogenide and @ad<"20030720" and (257/3).ccls. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/06 09:43 |
| S41 | 123 | chalcogenide and @ad<"20030720" and (257/4,5).ccls. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/06 10:43 |
| S42 | 121 | (ovonic\$ or chalcogenide) and @ad<"20030720" and (257/306, 505,246,295,200,296,748,536,103, 646,314,300,20).ccls. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/06 13:24 |
| S43 | 441 | (ovonic\$ or chalcogenide) and @ad<"20030720" and ("438").clas. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/06 13:24 |
| S44 | 2 | chalcogenide and memory and @ad<"20030720" and dielectric and electrode and "upper chalcogenide" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/06 15:06 |
| S45 | 18 | chalcogenide and memory and @ad<"20030720" and dielectric and electrode and "second chalcogenide" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/06 15:55 |
| S46 | 18 | chalcogenide and memory and @ad<"20030720" and dielectric and electrode and "first chalcogenide" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/06 15:38 |

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| S47 | 445 | chalcogenide and memory and @ad<"20030720" and dielectric and electrode and two adjchalcogenide\$ | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/06 15:39 |
| S48 | 7 | chalcogenide and memory and @ad<"20030720" and dielectric and electrode and two adj chalcogenide\$ | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/06 15:40 |
| S49 | 7 | chalcogenide and memory and @ad<"20030720" and dielectric and electrode and both adj chalcogenide\$ | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/06 15:41 |
| S50 | 387 | (ovonic or chalcogenide or pcm or "phase change material") and memory and @ad<"20030720" and dielectric and electrode and (second near3 layer) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/06 16:31 |
| S51 | 182 | fricke.in. and memory | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/06 16:31 |
| S52 | 4 | ("5282158" "6061264" "6229733" "6512284").PN. OR ("6870751").URPN. | US-PGPUB; USPAT; USOCR | OR | OFF | 2005/09/08 16:34 |
| S53 | 15 | "phase change resistor" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/09/09 08:27 |
| S54 | 95 | "257".clas. and "tapered via" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/09/09 08:27 |